

# Analog Electronic Circuits (UEC301)

By



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**THAPAR INSTITUTE**  
OF ENGINEERING & TECHNOLOGY  
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# Subject: Analog Electronic Circuits (UEC301)

Faculty names: Dr. Mayank Kumar Rai ( Associate Professor & Course Coordinator)

Topic of today's Lecture : BJT Biasing-I

## Key points

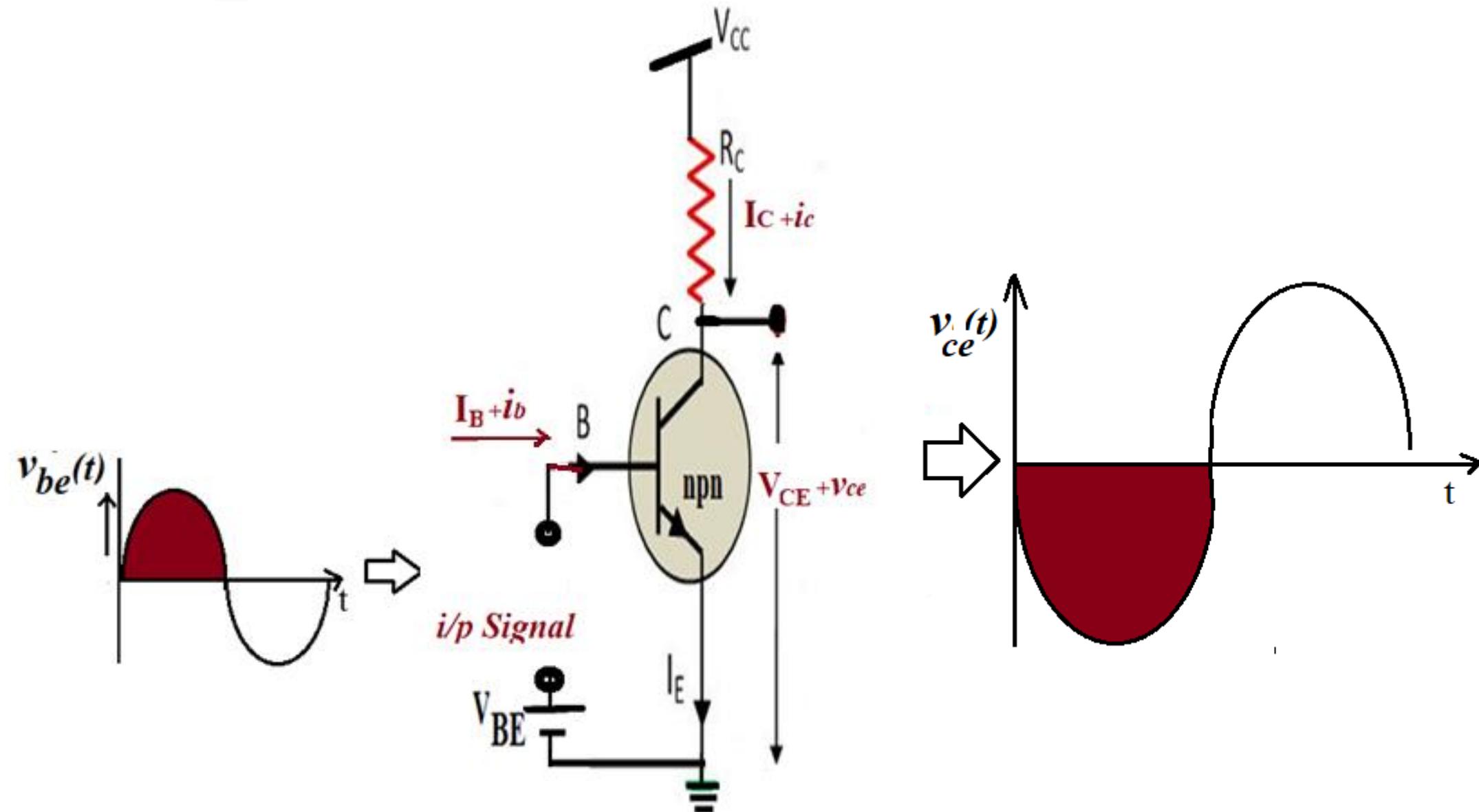
- ✓ Purpose of Transistor Biasing
- ✓ DC operating Points(i/p and o/p)
- ✓ Effects of Bias point location on Allowable Signal Swing
- ✓ Stabilization against Variations in  $I_{CO}$  and  $\beta$

Contents of this lecture are based on the following books:

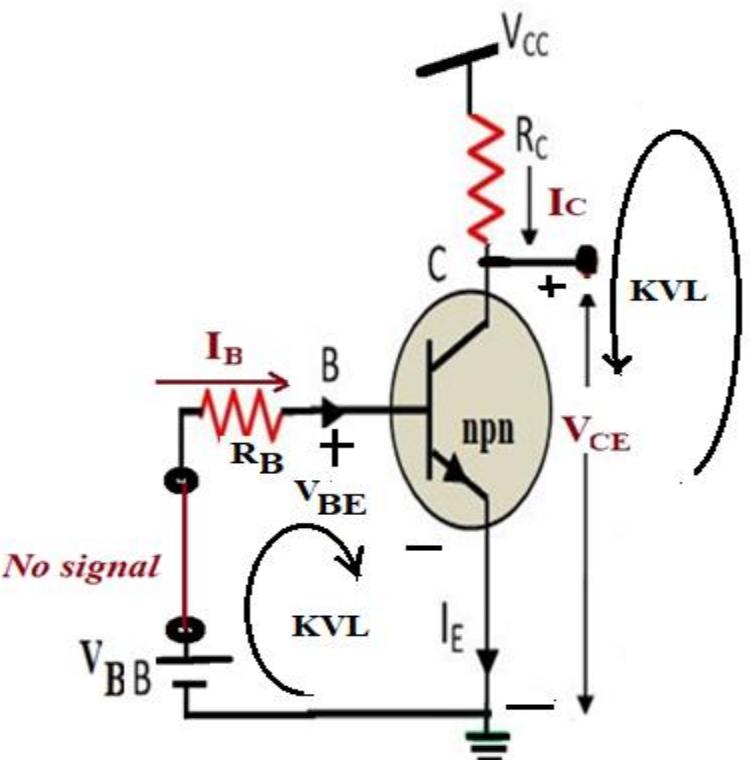
- Jacob Milman & and C.C.Halkias, "*Integrated Electronics Analog and Digital Circuit and Systems*" Second Edition.
- Adel S. Sedra & K. C. Smith, "*MicroElectronic Circuits Theory and Application*" Fifth Edition.
- Robert L. Boylestad & L. Nashelsky, "*Electronic Devices and Circuit Theory*" Eleventh Edition.



# Purpose of Transistor Biasing



# DC operating Points(i/p and o/p)

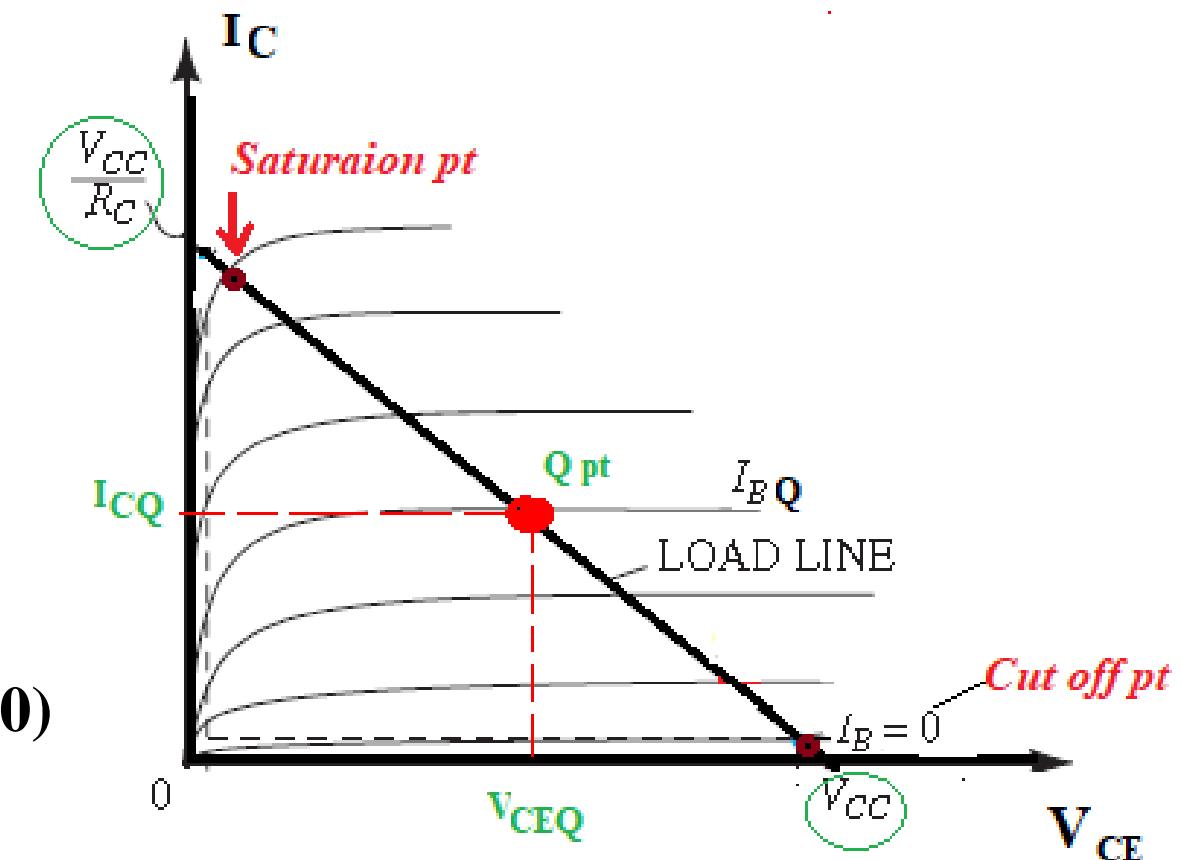


Output Char.

$$V_{CE} = V_{CC} - I_C R_C \dots (2)$$

$$V_{CE} = V_{CC} \text{ when } (I_C = 0)$$

$$I_C = V_{CC}/R_C \text{ when } (V_{CE} = 0)$$

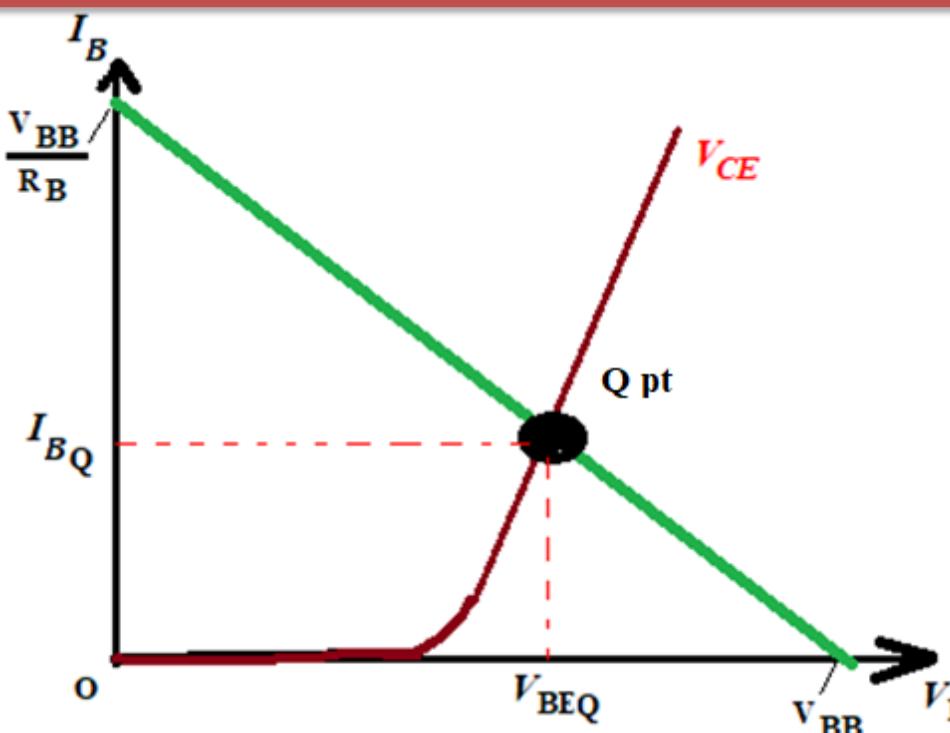


Input char.

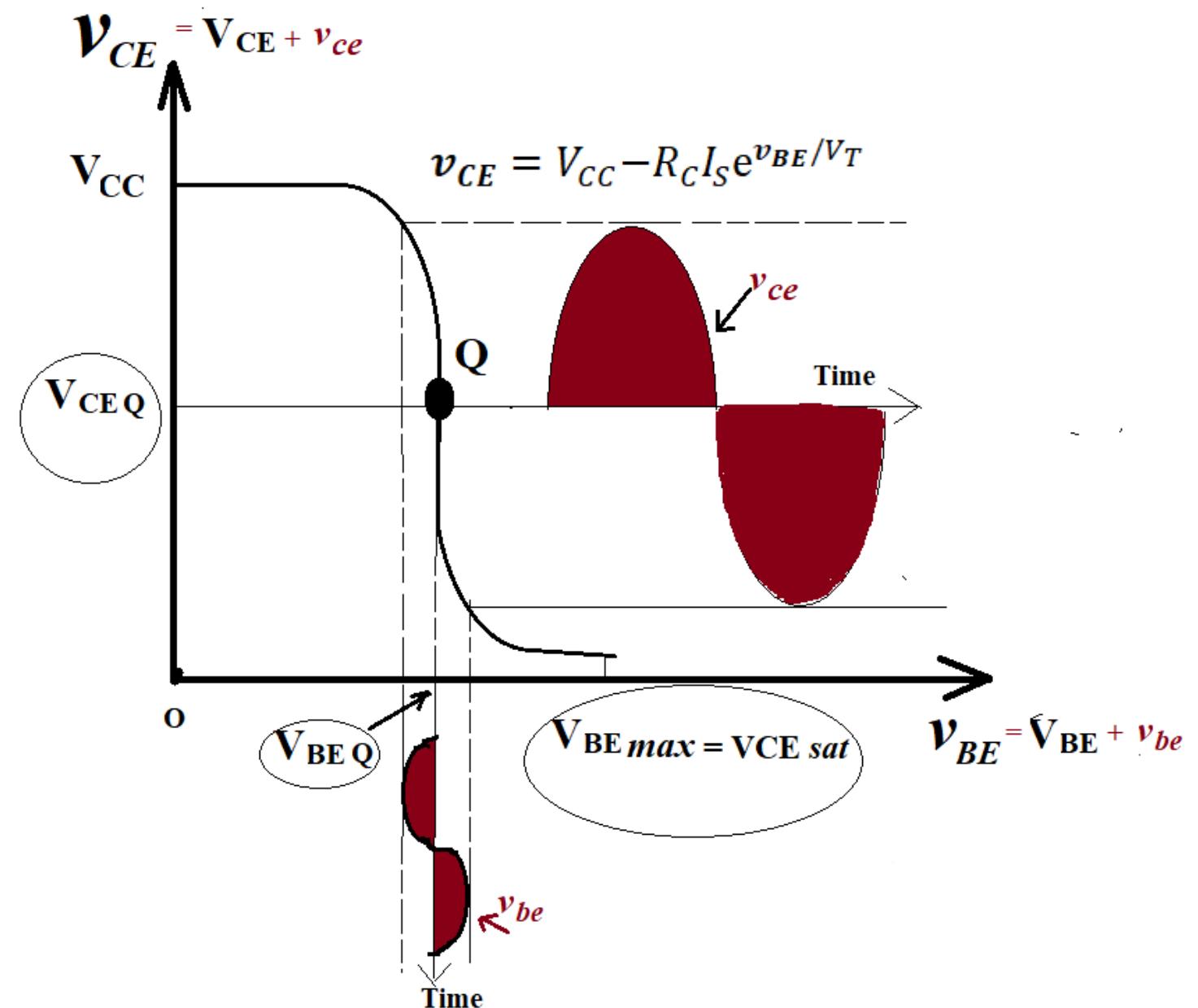
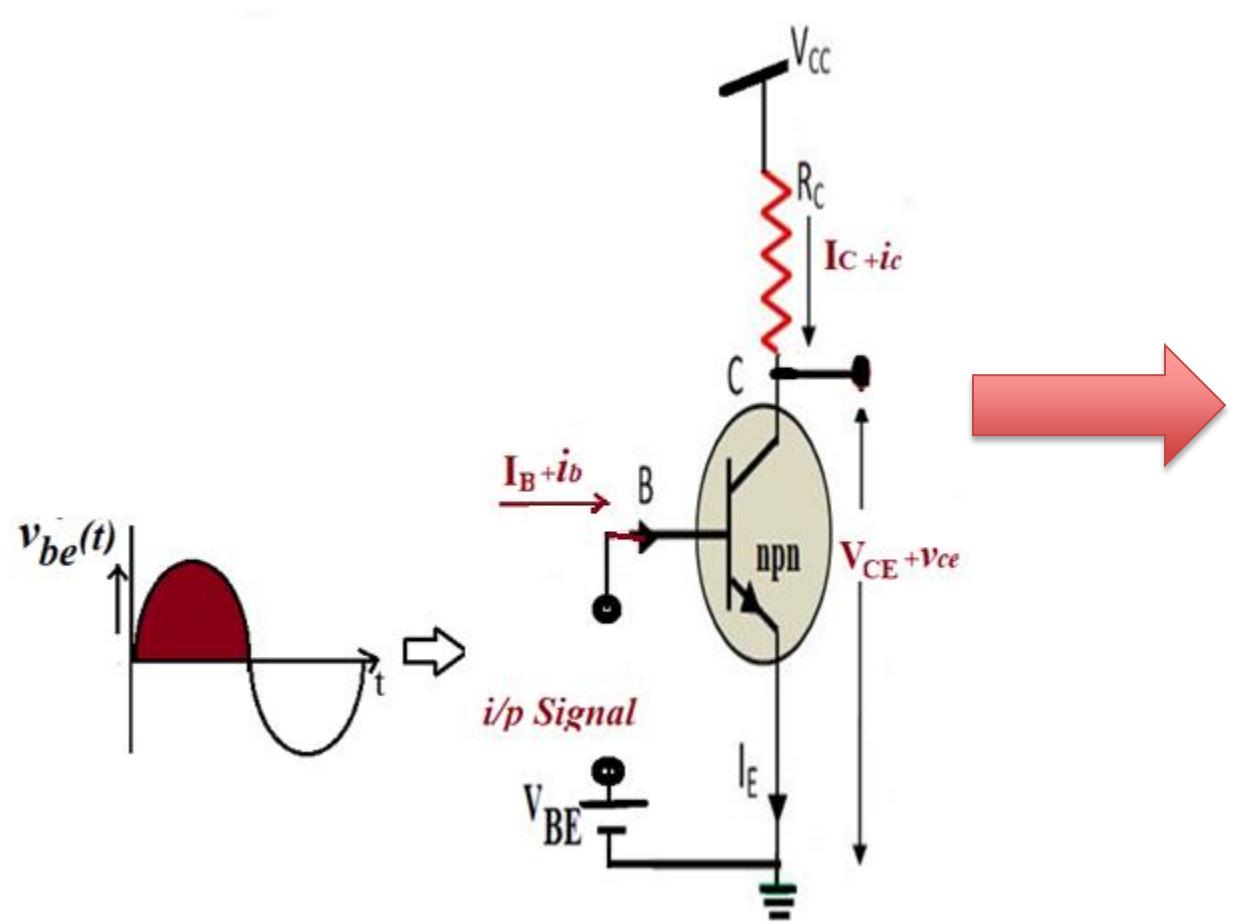
$$V_{BB} = V_{BE} + I_B R_B \dots (1)$$

$$V_{BE} = V_{BB} \text{ when } (I_B = 0)$$

$$I_B = V_{BB}/R_B \text{ when } (V_{BE} = 0)$$



# Transfer characteristic of the CEC based CKT, biased at Q point

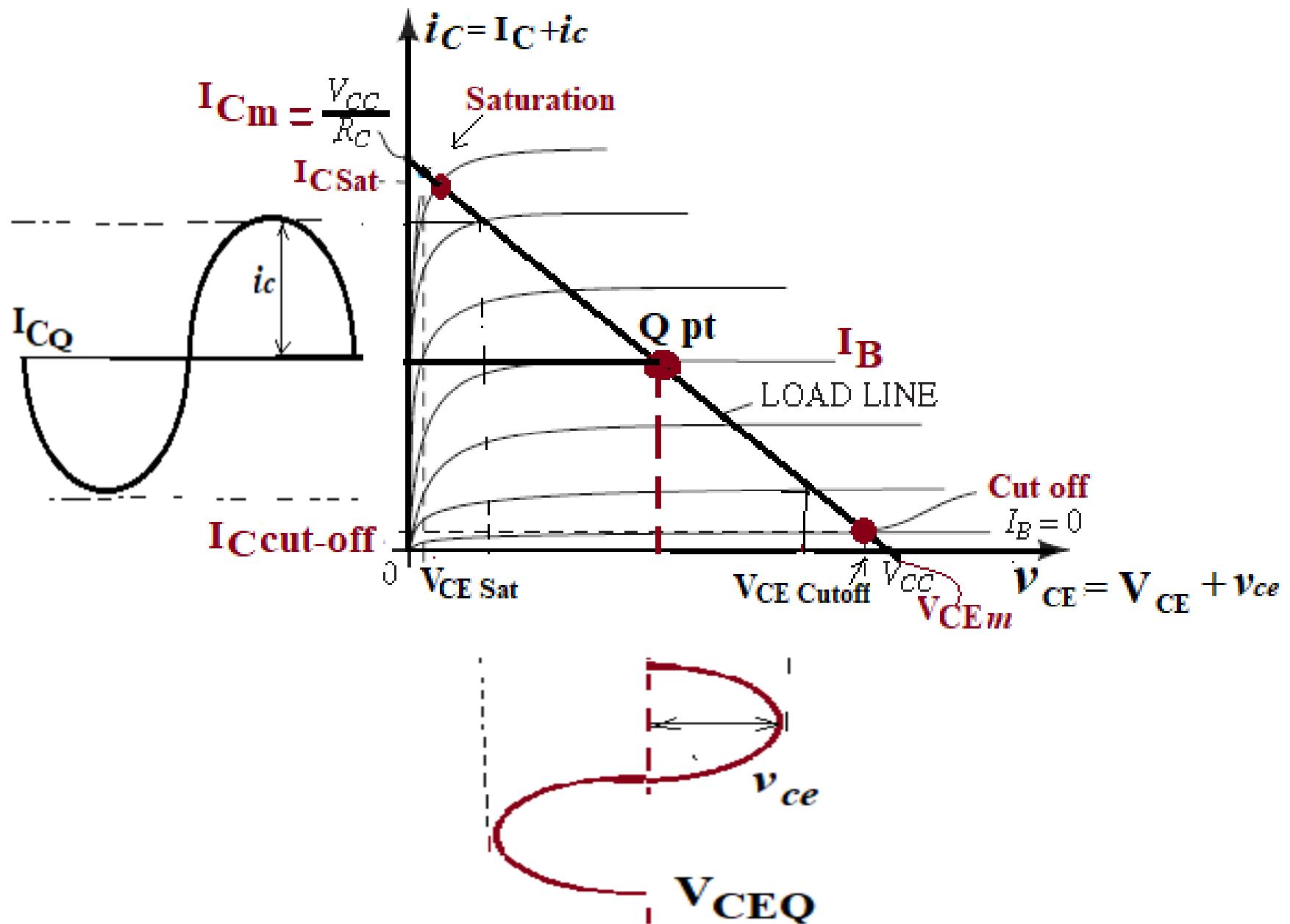


$$v_{CE} = V_{CC} - R_C i_c$$

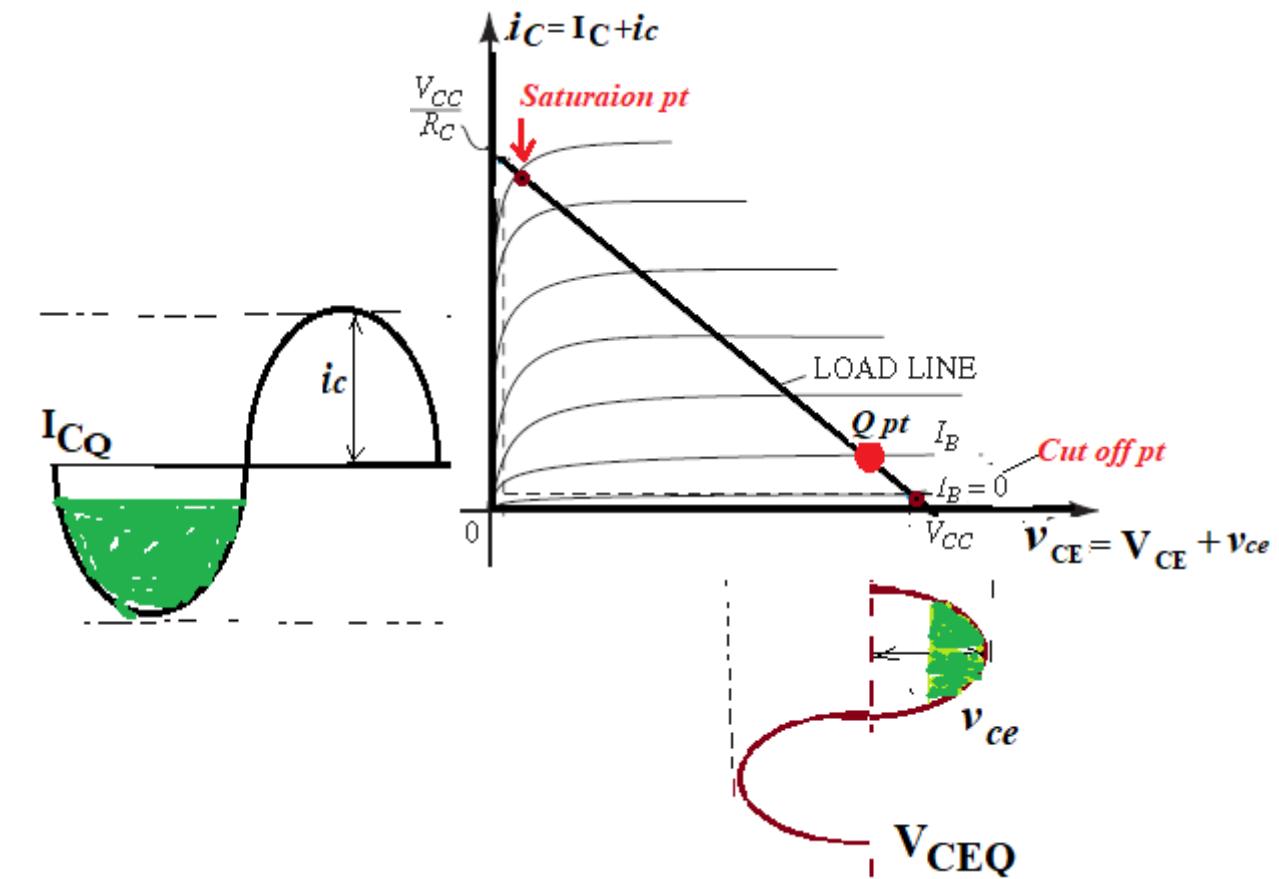
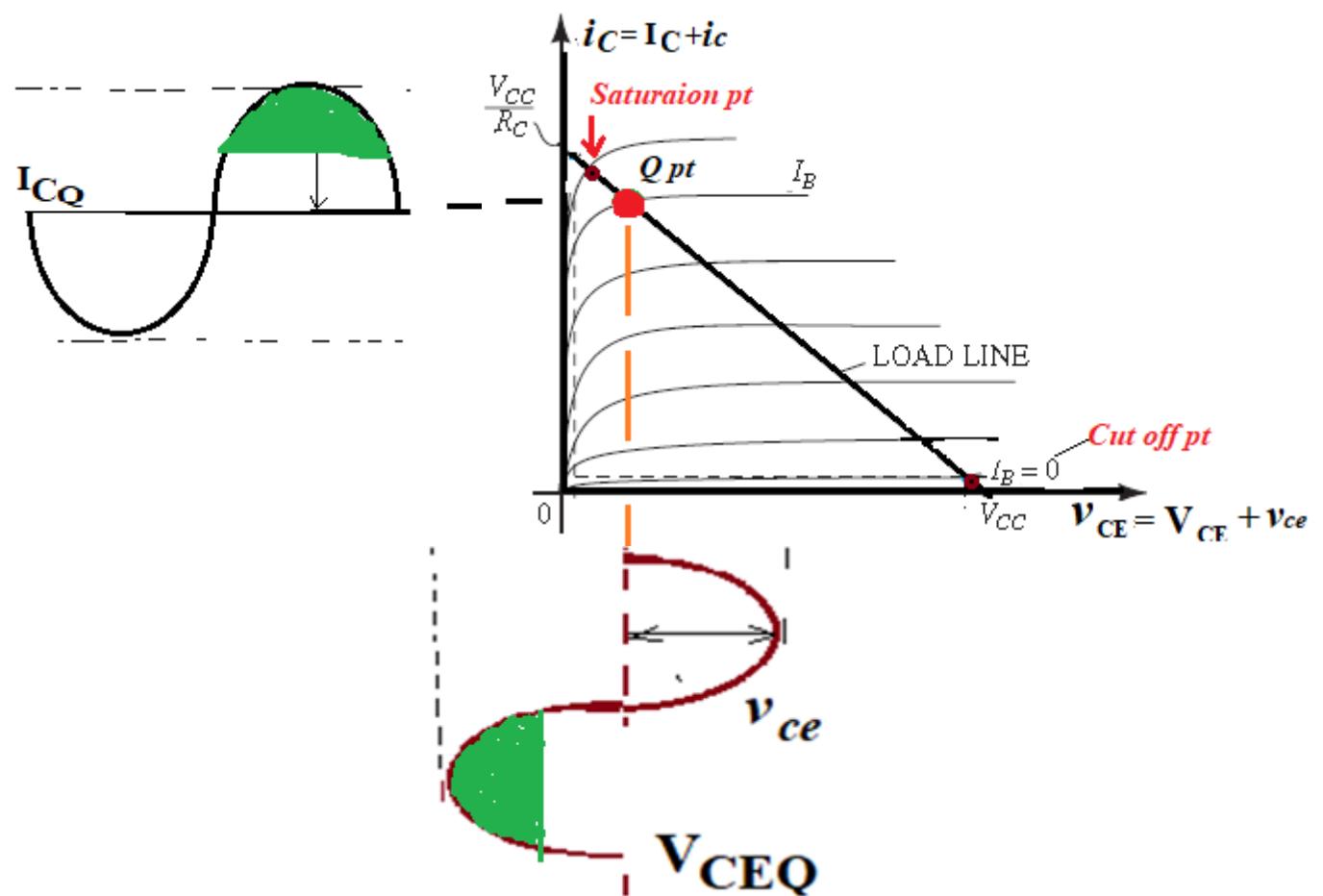
$$i_c \approx I_S e^{v_{BE}/V_T}$$

$$v_{CE} = V_{CC} - R_C I_S e^{v_{BE}/V_T}$$

# Output characteristic of the CEC based CKT, biased at Q point



# Effects of Bias point location on Allowable Signal Swing



# Stabilization against Variations in $I_{CO}$ and $\beta$

## Stabilisation of Q pt.

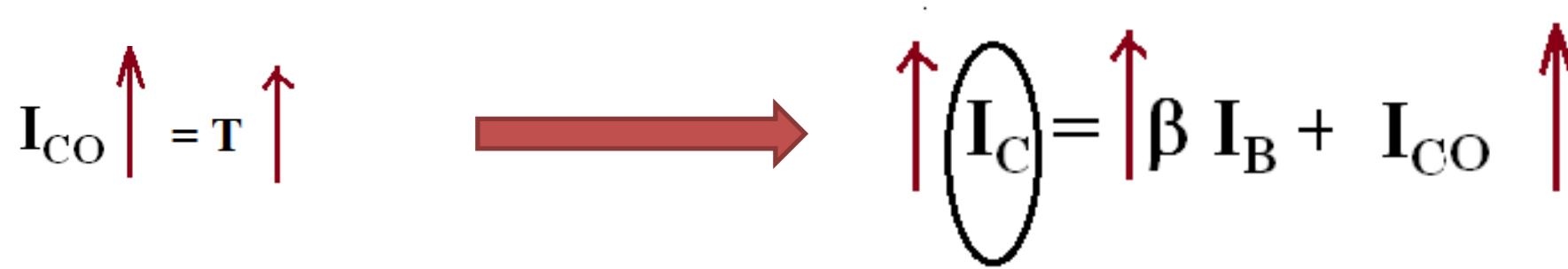
The collector current in transistor changes rapidly when: *The temperature changes,*

$$I_C = \beta I_B + I_{CO} \quad \dots(i)$$

$\beta$  &  $I_{CO}$  = function of temperature

$$\text{Stability Factor } (S) = dI_C/dI_{CO}$$

## Thermal Runway



*Thank You*

